



Features

- Floating high-side driver in bootstrap operation to 600V
- Drives two N-channel MOSFETs or IGBTs in high-side/low-side configuration
- Outputs tolerant to negative transients
- Wide low-side gate driver and logic supply: 10V to 20V
- Logic inputs CMOS and TTL compatible (down to 3.3V)
- Schmitt triggered logic inputs with internal pull down
- Undervoltage lockout for V_{CC} and V_B
- Space-saving SOIC-8 package
- Extended temperature range: -40degC to +125degC
- Drop-in replacements for IR2101

Description

The TF2101 is a high voltage, high speed gate driver capable of driving N-channel MOSFETs and IGBTs in a high-side/low-side configuration. Telefunken's high voltage process enables the TF2101's high-side to switch to 600V in a bootstrap operation. The 50ns (max) propagation delay matching between the high and the low side drivers allows high frequency switching.

The TF2101 logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) for easy interfacing with controlling devices. The driver outputs feature high pulse current buffers designed for minimum driver cross conduction.

The low-side gate driver and logic share a common ground to enable a space-saving 8-pin SOIC package and an 8-pin PDIP.

The TF2101 operates over an extended -40°C to +125°C temperature range.

Applications

- DC-DC Converters
- AC-DC Inverters
- Motor Controls
- Class D Power Amplifiers

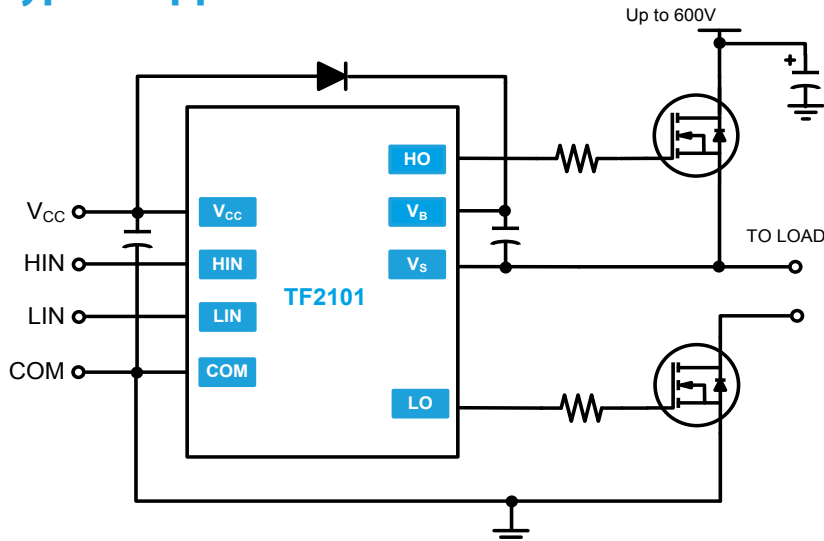


Ordering Information

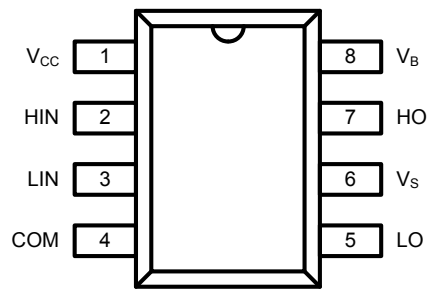
Year Year Week Week

PART NUMBER	PACKAGE	PACK / Qty	MARK
TF2101-TAU	SOIC-8(N)	Tube / 95	TF YYWW TF2101 Lot ID
TF2101-3AS	PDIP-8	Tube / 50	TF YYWW TF2101 Lot ID

Typical Application



Pin Diagrams



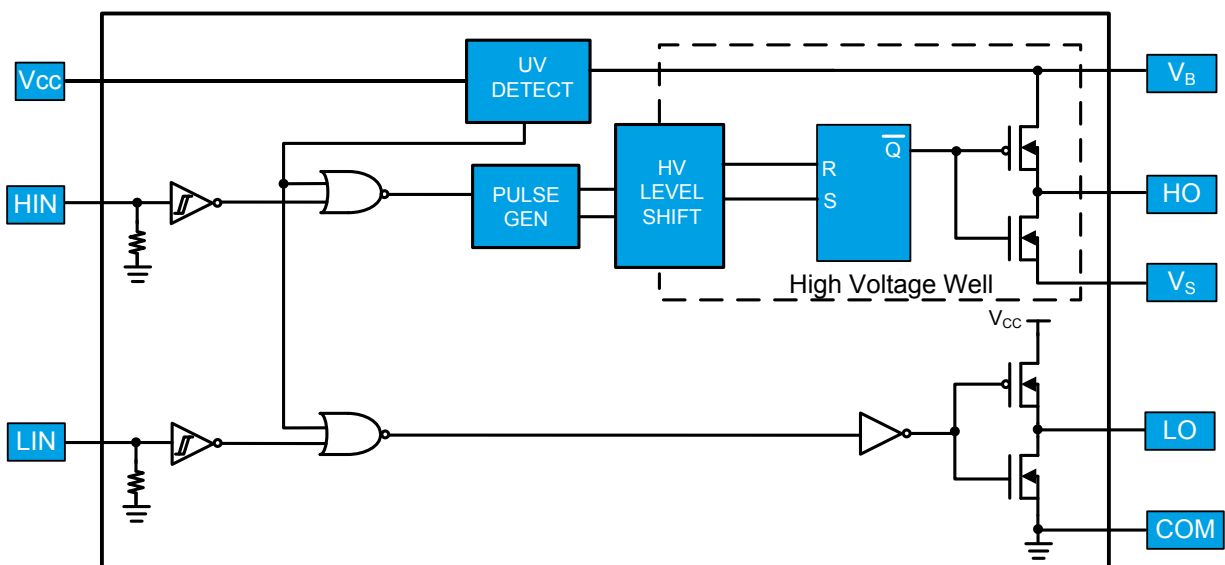
Top View: PDIP-8, SOIC-8

TF2101

Pin Descriptions

PIN NAME	PIN DESCRIPTION
HIN	Logic input for high-side gate driver output (HO), in phase
LIN	Logic input for low-side gate driver output (LO), in phase
V _B	High-side floating supply
HO	High-side gate drive output
V _S	High-side floating supply return
V _{CC}	Low-side and logic fixed supply
LO	Low-side gate drive output
COM	Low-side return

Functional Block Diagram



Absolute Maximum Ratings (NOTE1)

V_B - High side floating supply voltage.....-0.3V to +625V
 V_S - High side floating supply offset voltage... V_B -25V to V_B +0.3V
 V_{HO} - High side floating output voltage..... V_S -0.3V to V_B +0.3V
 dV_S / dt - Offset supply voltage transient.....50 V/ns

V_{CC} - Low side and logic fixed supply voltage.....-0.3V to +25V
 V_{LO} - Low side output voltage.....-0.3V to V_{CC} +0.3V
 V_{IN} - Logic input voltage (HIN and LIN)... -0.3V to V_{CC} +0.3V

P_D - Package power dissipation at $T_A \leq 25^\circ\text{C}$
 SOIC-8.....0.625W
 PDIP-8.....1.0W

NOTE1 Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SOIC-8 Thermal Resistance (NOTE2)

θ_{JC}45 °C/W
 θ_{JA}200 °C/W

PDIP-8 Thermal Resistance (NOTE2)

θ_{JC}35 °C/W
 θ_{JA}125 °C/W

T_J - Junction operating temperature+150 °C

T_L - Lead temperature (soldering, 10s) +300 °C

T_{stg} - Storage temperature range-55 °C to +150 °C

ESD Susceptibility

HBM (NOTE3).....2 kV

MM (NOTE4).....200V

CDM (NOTES).....1.5 kV

NOTE2 When mounted on a standard JEDEC 2-layer FR-4 board.

NOTE3 Human Body Model, applicable standard JESD22-A114

NOTE4 Machine Model, applicable standard JESD22-A115

NOTE5 Field Induced Charge Device Model, applicable standard JESD22-C101

Recommended Operating Conditions

Symbol	Parameter	MIN	TYP	MAX	Unit
V_B	High side floating supply absolute voltage	$V_S + 10$		$V_S + 20$	V
V_S	High side floating supply offset voltage	NOTE6		600	V
V_{HO}	High side floating output voltage	V_S		V_B	V
V_{CC}	Low side and logic fixed supply voltage	10		20	V
V_{LO}	Low side output voltage	0		V_{CC}	V
V_{IN}	Logic input voltage (HIN and LIN)	COM		V_{CC}	V
T_A	Ambient temperature	-40		125	°C

NOTE6 Logic operational for $V_S = -5$ to +600V. Logic state held for $V_S = -5$ V to $-V_{BS}$.

DC Electrical Characteristics (NOTE7)

$V_{BIAS} (V_{CC}, V_{BS}) = 15V, T_A = 25^\circ C$, unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
V_{IH}	Logic "1" input voltage	$V_{CC} = 10V$ to $20V$	3			V
V_{IL}	Logic "0" input voltage	$V_{CC} = 10V$ to $20V$			0.8	V
V_{OH}	High level output voltage, $V_{BIAS} - V_O$	$I_O = 0A$			0.1	V
V_{OL}	Low level output voltage, V_O	$I_O = 0A$			0.1	V
I_{LK}	Offset supply leakage current	$V_B = V_S = 600V$			50	μA
I_{BSQ}	Quiescent V_{BS} supply current	$V_{IN} = 0V$ or $5V$		30	55	μA
I_{CCQ}	Quiescent V_{CC} supply current	$V_{IN} = 0V$ or $5V$		150	270	μA
I_{IN+}	Logic "1" input bias current	$V_{IN} = 5V$		3	10	μA
I_{IN-}	Logic "0" input bias current	$V_{IN} = 0V$			1	μA
V_{CCUV+}	V_{CC} supply under-voltage positive going threshold		8	8.9	9.8	V
V_{CCUV-}	V_{CC} supply under-voltage negative going threshold		7.4	8.2	9	V
I_{O+}	Output high short circuit pulsed current	$V_O = 0V, V_{IN} = \text{Logic "1"}, PW \leq 10 \mu s$	130	210		mA
I_{O-}	Output low short circuit pulsed current	$V_O = 15V, V_{IN} = \text{Logic "0"}, PW \leq 10 \mu s$	270	360		mA

AC Electrical Characteristics

$V_{BIAS} (V_{CC}, V_{BS}) = 15V, T_A = 25^\circ C$, and $C_L = 1000pF$, unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
t_{ON}	Turn-on propagation delay	$V_S = 0V$		160	220	ns
t_{OFF}	Turn-off propagation delay	$V_S = 600V$		150	220	ns
t_r	Turn-on rise time			100	170	ns
t_f	Turn-off fall time			50	90	ns
t_{DM}	Delay matching				50	ns

NOTE7 The V_{IH} , V_{TH} , and I_{IN} parameters are referenced to COM. The V_O and I_O parameters are referenced to COM and are applicable to the respective output pins: HO and LO.

Timing Waveforms

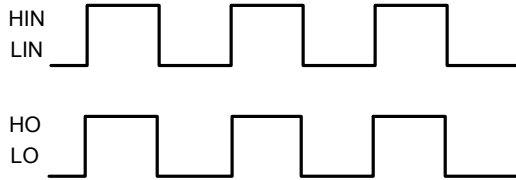


Figure 1. Input / Output Timing Diagram

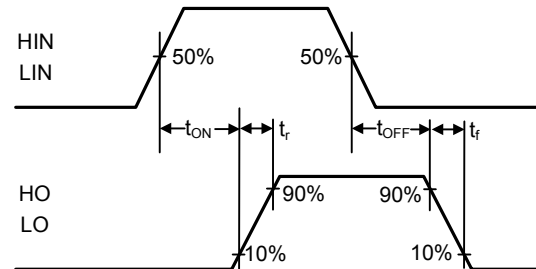


Figure 2. Switching Time Waveform Definitions

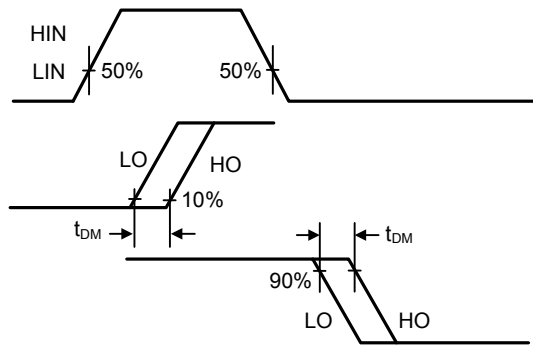
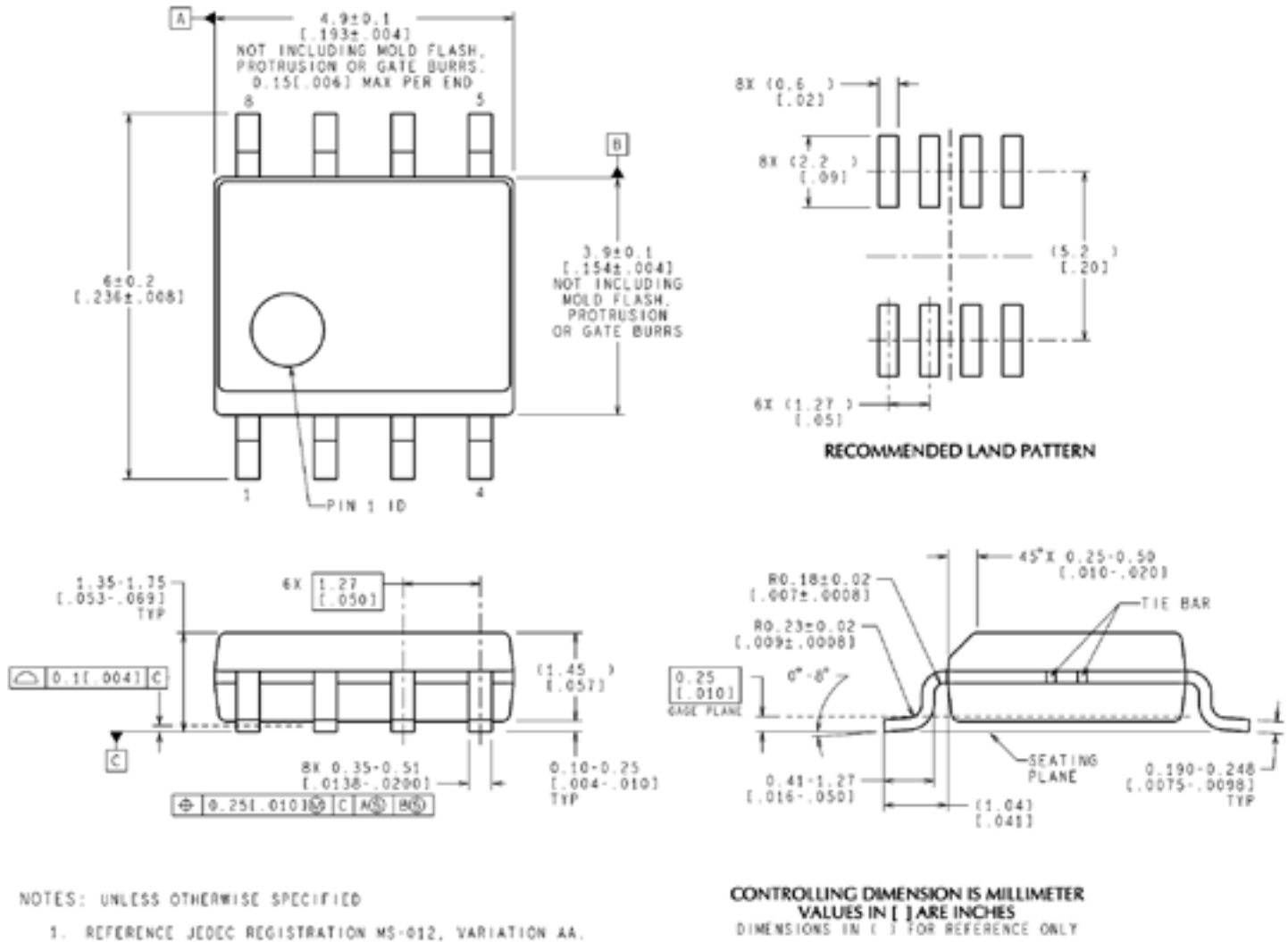


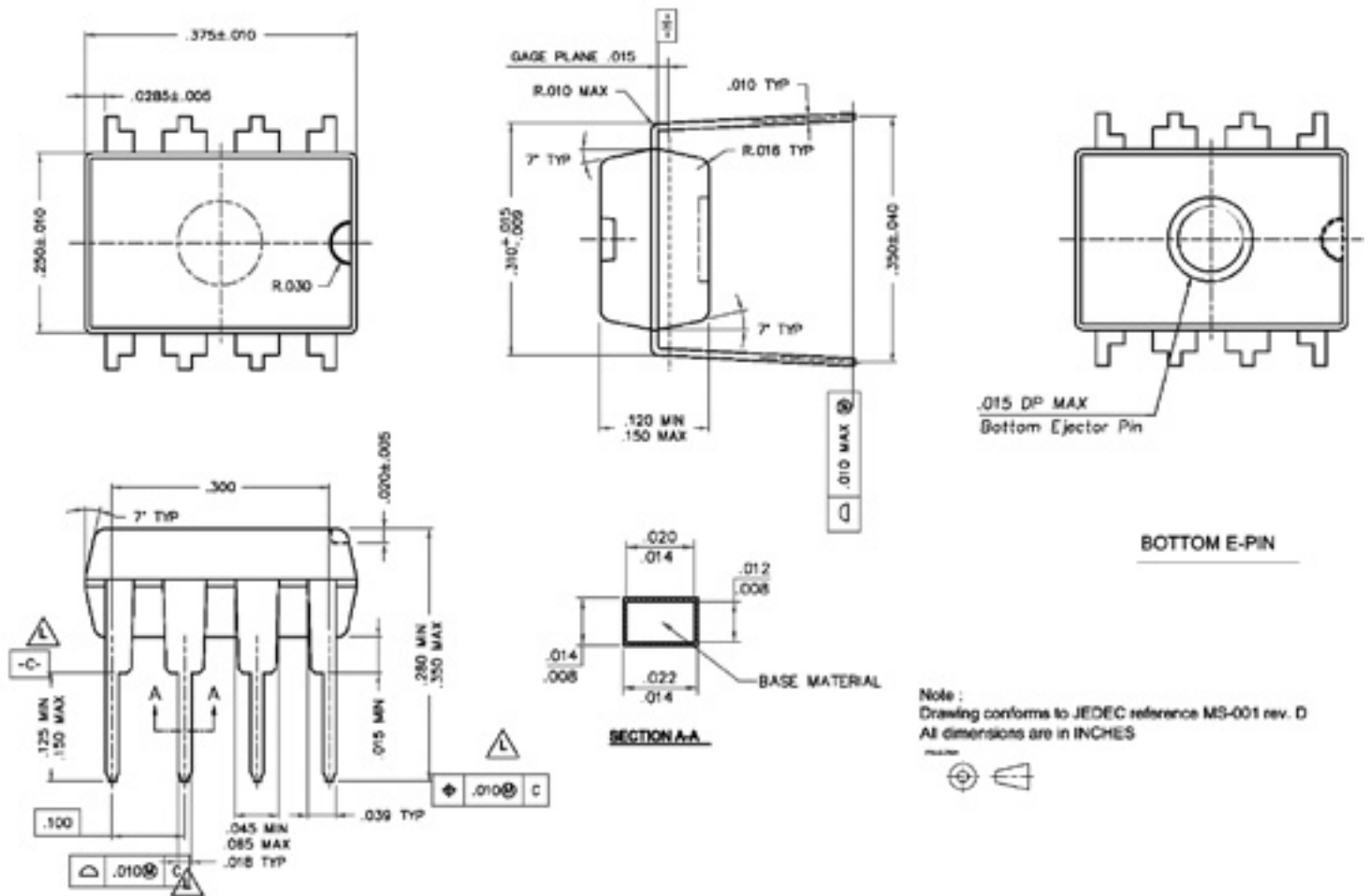
Figure 3. Delay Matching Waveform Definitions

Package Dimensions (SOIC-8 N)

Please contact support@telefunkensemi.com for package availability.



Package Dimensions (PDIP-8)



Notes

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